

## Insulated Gen 2 Schottky Rectifier Module, 250 A



PRIMARY CHARACTERISTICS						
$I_{F(AV)}$ per module at $T_C = 106$ °C	250 A					
$V_{R}$	200 V					
V <sub>FM</sub> at 200 A, T <sub>C</sub> = 25 °C	1.0 V					
Package	SOT-227					
Circuit configuration	Two separate diodes,					

#### **FEATURES**

- Max. T<sub>J</sub> = 175 °C
- Two fully independent diodes
- Fully insulated package
- Trench MOS Barrier Schottky technology
- Ultra low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- · Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION**

The VS-QA250FA20 insulated modules integrate two state of the art Trench MOS Schottky technology rectifiers in the compact, industry standard SOT-227 package.

These devices are thus intended for high frequency converters and switching power supplies.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
V <sub>F</sub>	T <sub>J</sub> = 125 °C	1.09	V		
T <sub>J</sub>	Range	-55 to +175	°C		

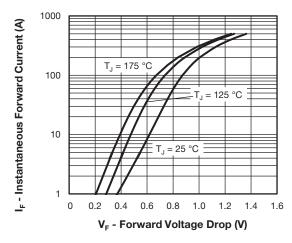
<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average forward current per module	I <sub>F(AV)</sub>	T <sub>C</sub> = 106 °C	250	Α	
Maximum cathode to anode voltage	$V_R$		200	V	
Maximum continuous forward current per diode	I <sub>F</sub>	T <sub>C</sub> = 95 °C	183	۸	
Maximum single pulse forward current per diode	I <sub>FSM</sub>	$T_C = 175$ °C, t = 6 ms, square	900	_ A	
Maximum power dissipation per diode	P <sub>D</sub>	T <sub>C</sub> = 95 °C	182	W	
Non-repetitive avalanche energy per diode	E <sub>AS</sub>	$T_J = 25  ^{\circ}\text{C},  I_{AS} = 19  \text{A},  L = 10  \text{mH}$	1800	mJ	
RMS isolation voltage	V <sub>ISOL</sub>	Any terminal to case, t = 1 minute	2500	V	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

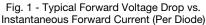


<b>ELECTRICAL SPECIFICATIONS PER DIODE</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 2 mA	200	-	-	
Forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 200 A	-	1.0	1.2	V
Forward voltage		I <sub>F</sub> = 200 A, T <sub>J</sub> = 125 °C	-	0.89	1.09	
Reverse leakage current	Davisius la classica surrent	V <sub>R</sub> = 200 V	-	13	90	μΑ
Reverse leakage current	T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	14	-	mA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	380	-	pF

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	+	T <sub>J</sub> = 25 °C		-	54	-	nc
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	$I_F = 50 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}$	-	67	-	ns
Dook recovery current	ak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	6	-	А
Feak recovery current		T <sub>J</sub> = 125 °C		-	8.4	-	
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	165	-	nC
	T <sub>J</sub> = 125 °C		-	296	-	IIC IIC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	Б		-	-	0.44	
Junction to case, both leg conducting	$R_{thJC}$		-	-	0.22	°C/W
Case to heatsink	R <sub>thCS</sub>	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting toward		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SC	T-227	





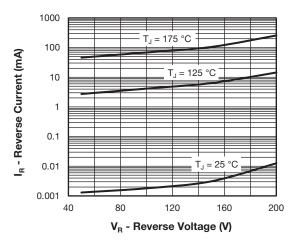


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

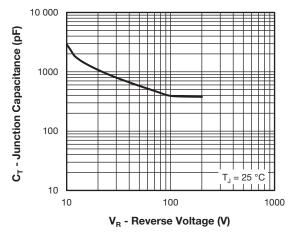


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

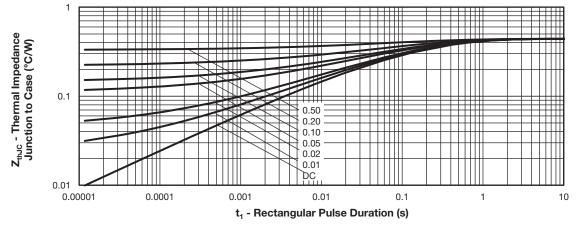


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Diode)



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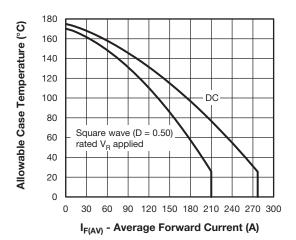


Fig. 5 - Maximum Current Rating Capability (Per Diode)

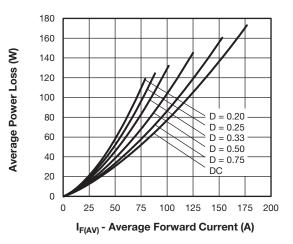


Fig. 6 - Forward Power Loss Characteristics (Per Diode)

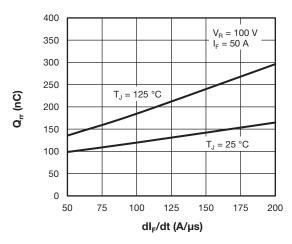


Fig. 7 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt (Per Diode)

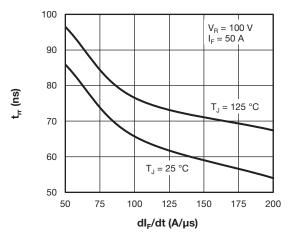


Fig. 8 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Diode)

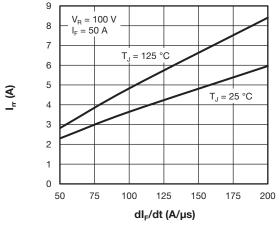


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt (Per Diode)

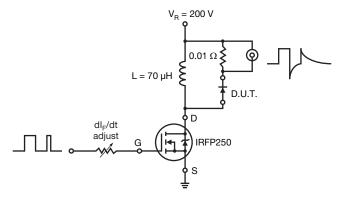
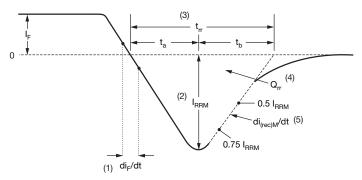


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

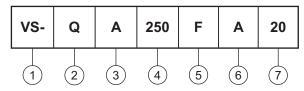
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 11 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

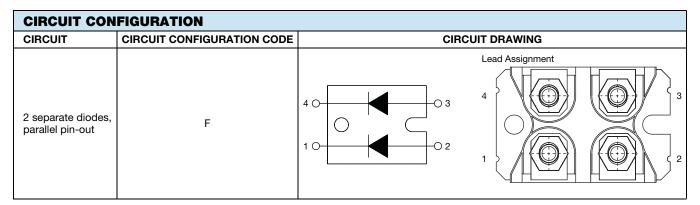
**Device code** 



- Vishay Semiconductors product
- 2 Schottky technologies
- 3 Present silicon generation
- 4 Current rating (250 = 250 A)
- 5 Circuit configuration (2 separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (20 = 200 V)

Quantity per tube is 10, M4 screw and washer included

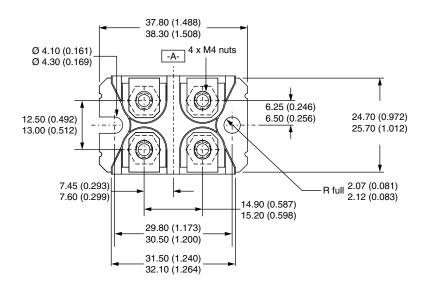


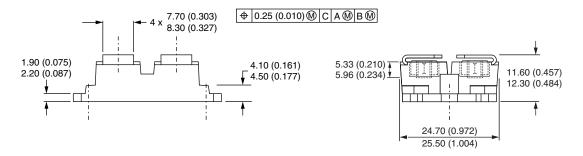


LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95423</u>					
Packaging information	www.vishay.com/doc?95425				

### SOT-227 Generation 2

#### **DIMENSIONS** in millimeters (inches)





#### Note

· Controlling dimension: millimeter



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